ABSTRACT OF THE DISCLOSURE

When the Cu-containing aluminum film is dry-etched with etching gas containing chlorine gas, the gas stay time τ of the etching gas staying in the chamber, which is expressed by P·V/Q, where P being the chamber pressure (unit: Pa), V the chamber volume (unit: L) and Q the total flow of etching gas (unit: Pa · L/sec), is from 0.15 seconds to 0.30 seconds inclusive.

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